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PATENT ABSTRACTS OF JAPAN

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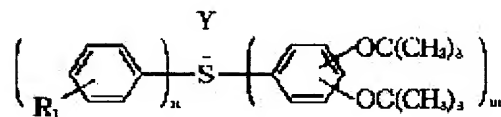
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(54) CHEMICALLY SENSITIZED POSITIVE RESIST MATERIAL

(57)Abstract:

PURPOSE: To provide a chemically sensitized positive resist material which has a high sensitivity against high energy beam radiation such as far ultraviolet rays, electron beam, and X-rays, and by which pattern formation can be made by developing it with an alkali aqueous solution, so that it is suitable for fine working technique.

CONSTITUTION: A chemically sensitized positive resist material is that which includes a new sulfonium salt as shown by the formula. In the formula, R1 denotes a hydrogen atom, alkyl group, alkoxyl group or dialkylamino group, and Y denotes trisulfomethanesulfonate or p-toluensulfonate. The n is an integer of 0 to 2, m is an integer of 1 to 3, and n+m=3.



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